Abstracts

Broadband Monolithic Low-Noise Feedback Amplifiers (1983 [MWSYM])

P.N. Rigby, J.R. Suffolk and R.S. Pengelly. "Broadband Monolithic Low-Noise Feedback Amplifiers (1983 [MWSYM])." 1983 MTT-S International Microwave Symposium Digest 83.1 (1983 [MWSYM]): 41-45.

A 0.6 to 6 GHz monolithic GaAs FET low-noise feedback amplifier has been developed. This amplifier chip has a gain of 6 dB and a noise figure of around 4 dB over the bandwidth. Gains of 8 dB have been-achieved at ½I /sub dss/ with 1 dB gain compression points of 21 dBm over the band. This paper discusses the design of such amplifiers using as an example a 1 to 10 GHz two stage monolithic amplifier chip presently under development which is capable of being cascaded up to total gains of 50 dB or so with ± 1.5 dB ripple.

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